

Electronic Supplementary Information (ESI) for

**Roles of spin-state dangling bonds and strain on the electronic structure of
polytetrafluoroethylene for charge transfer from first-principles**

SeongMin Kim* ^{a,b}, So-Hee Kim^a and Sang-Woo Kim* ^{a,b}

^aDepartment of Materials Science and Engineering, Center for Human-oriented Triboelectric
Energy Harvesting, Yonsei University, Seoul 03722, Republic of Korea

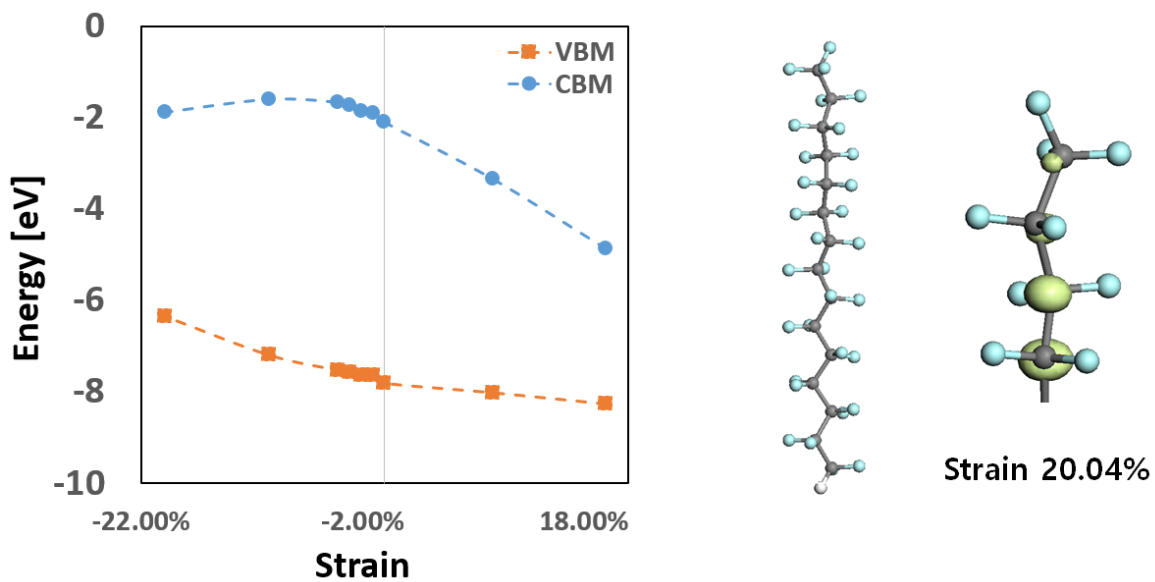
^bDepartment of Battery Engineering, Yonsei University, Seoul 03772, Republic of Korea

*Corresponding authors.

E-mail addresses: smkim417@gmail.com (S.M.K), kimsw1@yonsei.ac.kr (S.-W.K).

28

29 **Supplement figure captions**



30

31

32 **Figure S1.** A plot of CBM/VBM for reference PTFE slab as a function of strain (-20% ~ 20%).

33 Note that the orbital was shown for the PTFE under a strain of 20.04%.

34

35

36

37

38

39

40

41

42

43

44

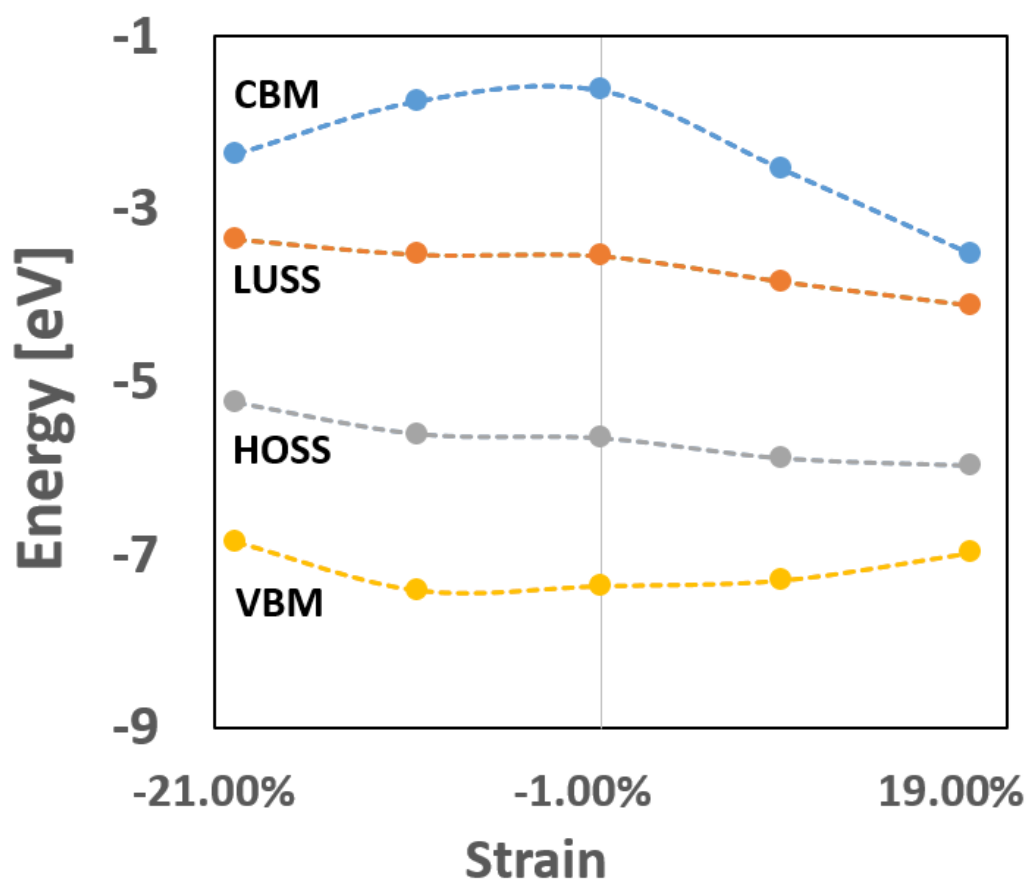


Figure S2. A plot of CBM, LUSS, HOSS, and VBM for the 1DB PTFE slab as a function of strain (-20% ~ 20%).

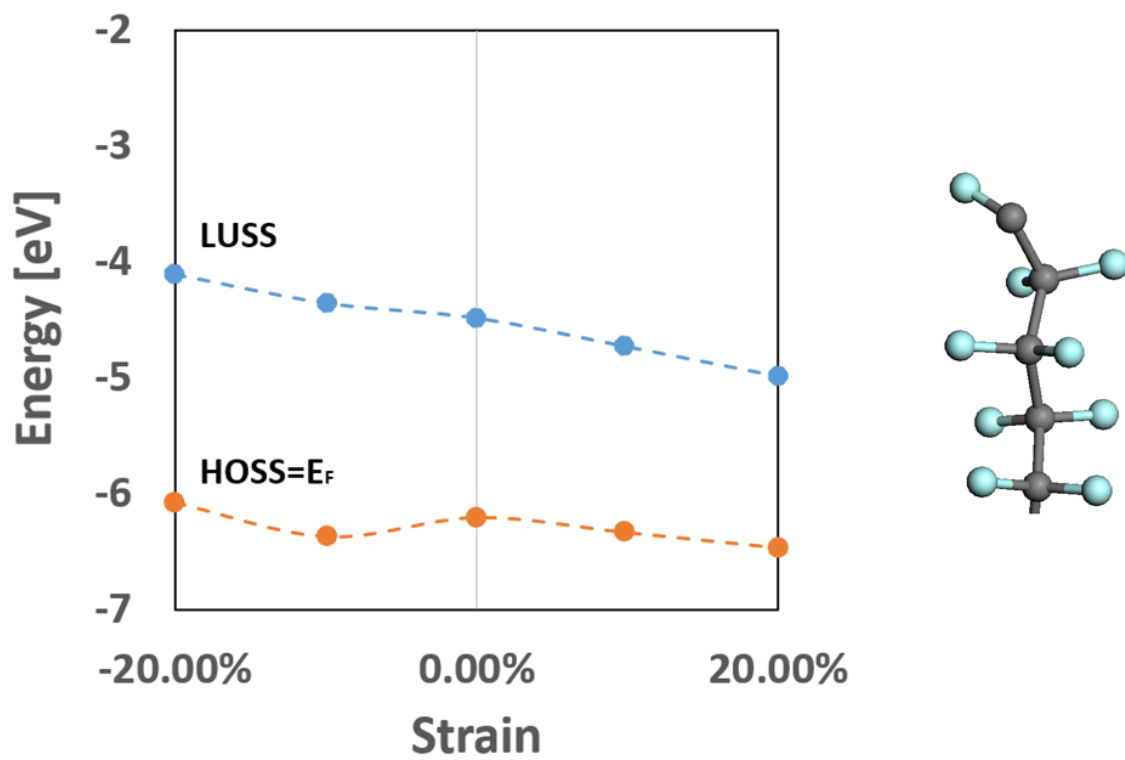
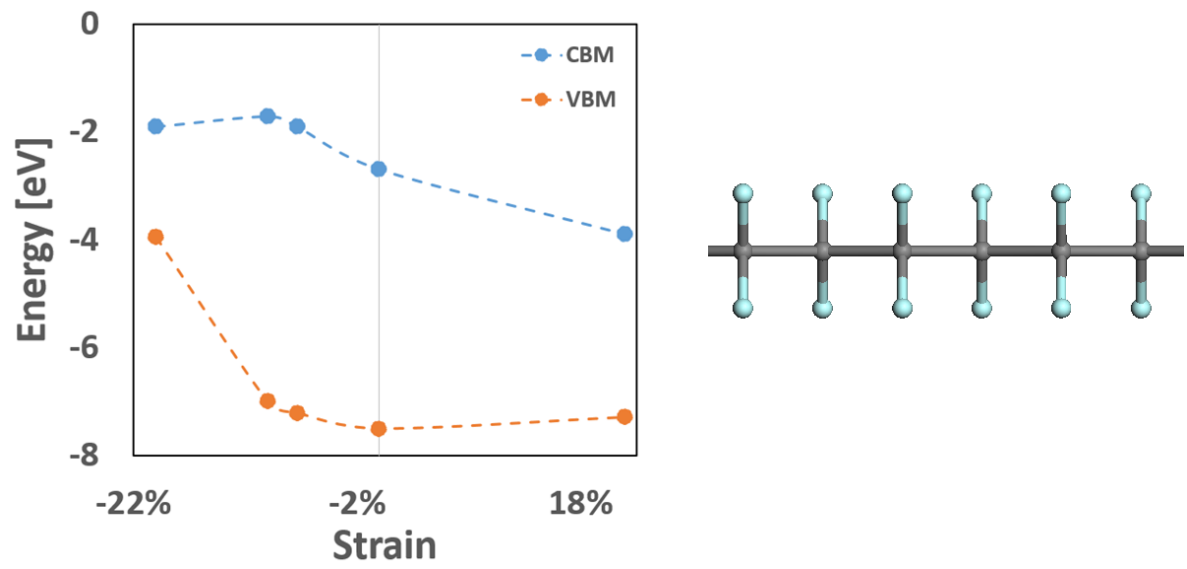


Figure S3. A plot of LUSS and HOSS for the 2DB PTFE slab as a function of strain (-20% ~ 20%).

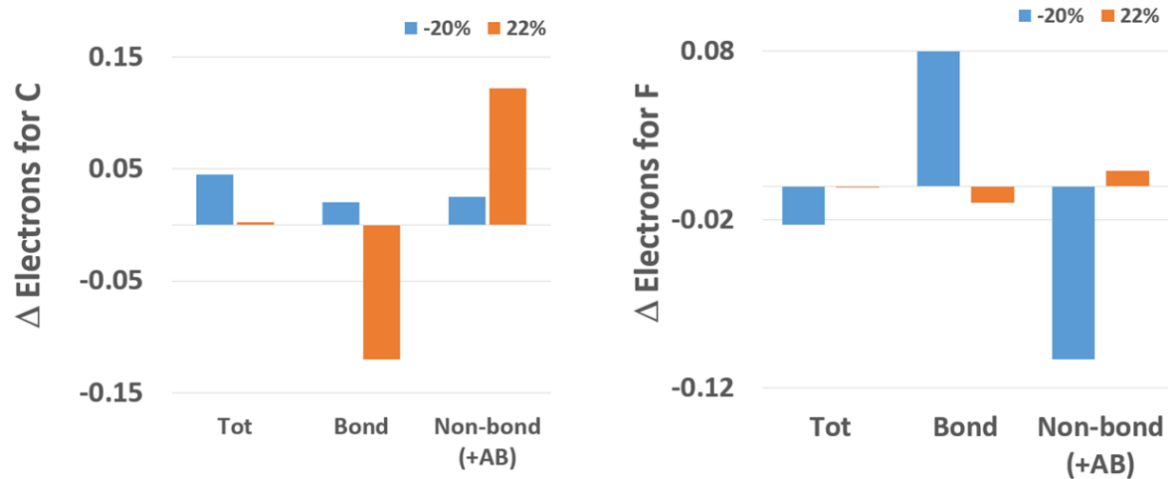


73

74

75 **Figure S4.** A plot of CBM and VBM for the 2_1 1-dimensional PTFE as a function of strain (-
 76 20% ~ 20%).

77



78

79

80 **Figure S5.** A plot of the change in the number of electrons for C and F in 2₁ 1D PTFE. Note
 81 that for compression (-20%), electrons are transferred from F to C, and for elongation (20%),
 82 non-bonding electrons increase for C.

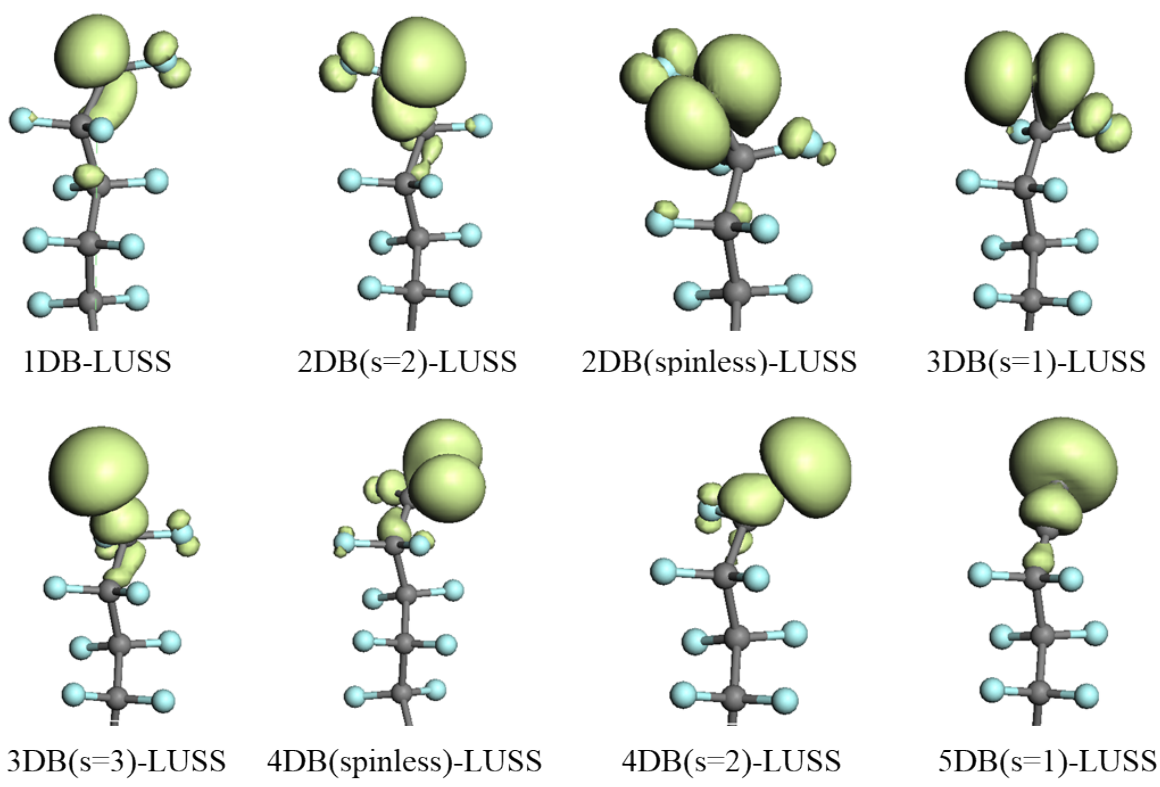


Figure S6. Shape of the acceptor orbitals.

87 **Note. 1. Methodology of DFT**

88 DFT calculations were performed using the CASTEP code, with the method detailed below. A
89 2D slab and contact model were used, incorporating a vacuum region exceeding 15 Å to avoid
90 interactions between periodic images, along with a dipole correction to minimize spurious
91 interactions. A TS semi-empirical dispersion correction was applied to account for long-range
92 energy, and when the band gap was underestimated by GGA, meta-GGA (RSCAN) and hybrid
93 XC functionals, such as HSE06 and PBE0, were used to correct for self-interaction errors in
94 GGA. The on-the-fly-generation (OTFG) ultrasoft pseudopotential, implemented in Materials
95 Studio, was used to calculate electron-ion interactions by treating the pseudovalence electrons
96 of atoms. Structural optimization for the 1D PTFE polymer model was performed with the PBE
97 functional under the BFGS line-search algorithm, using Monkhorst-Pack special k-points for
98 Brillouin zone integration. A cutoff energy of 440 eV was applied for the plane wave basis set
99 during electronic minimization, and a vacuum region of more than 20 Å was employed to
100 prevent interactions between neighboring cells. The geometric optimization was performed
101 with convergence criteria for energy, force, and displacement set to 1×10^{-5} eV/atom, 0.03 eV/
102 Å, and 0.001 Å, respectively. Density of states (DOS) and band structure calculations were
103 carried out with k-spacing values of 0.04 and 0.015 Å⁻¹. To correct band gap underestimation,
104 hybrid exchange-correlation functionals were used with the GGA-derived wavefunctions and
105 densities. Collinear spin polarization was applied for surface state (SS) modelling, optimizing
106 spin states for unpaired electrons in various configurations. The combination of these advanced
107 computational techniques provided accurate predictions of electronic properties and surface
108 states, contributing to a deeper understanding of the material's behavior in various
109 environments.

110

Defect type	Defect formation energy (eV)	Comparable chemical bond energy (eV)	Notes
Removal of 1F atom	4.2	C-H bond (~4.3 eV) / Si-Si bond (~3.6 eV)	Similar to the dissociation energy of a single bond
Removal of 2F atoms	8.3	C=C double bond (~6.3 eV) / C-O bond (~7.6 eV)	Higher than most double bonds
Removal of 3F atoms	12.8	C≡C triple bond (~12.6 eV) / Hydrogen ionization energy (~13.6 eV)	Comparable to ionizing hydrogen
Strain Formation (20% axial strain)	7-8	-	Comparable to defect formation of 2F atoms

111 **Table 1.** Defect formation energy and comparison with chemical bond energies

112

System	Slab length (Å)	Length increase (Å)	Strain formation energy (eV)	Axial strain (%)
Ref.	20.437	4.087	8.15	20
1DB	19.333	3.87	7.60	20
2DB	19.223	3.845	7.43	20

113 **Table. 2.** Strain formation energy and slab length changes with axial strain of 20%